

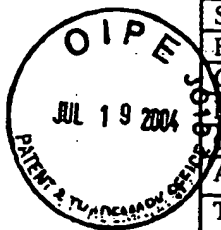
First Named Inventor	Leonard Forbes	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
Serial No.	10/775,424	
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Group Art Unit	2655	
Examiner Name	Unknown	
Confirmation No.	9726	
Attorney Docket No.	400.270US01	
Title: NR0M FLASH MEMORY CELL WITH INTEGRATED DRAM		Sheet 1 of 7

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INTEGRATED DRAM		

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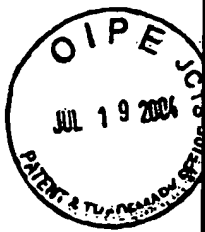


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